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### N-Channel 40 V (D-S) MOSFET

# PRODUCT SUMMARY $V_{DS}$ (V) $R_{DS(on)}$ (mΩ)(Typ.) $I_D$ (A)a $Q_g$ (Typ.) 40 2.2 at $V_{GS}$ = 10 V 125 40.4 nC

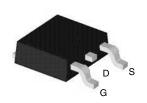
#### **FEATURES**

- DT-Trench Power MOSFET
- 100 %  $R_g$  and UIS Tested
- High density cell design for ultra low Rdson
- · AEC-Q101 Qualified for Automotive Applications

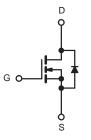
#### **APPLICATIONS**

- · Load switching
- · Hard switched and high frequency circuits





Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	40	V	
Gate-Source Voltage			± 20	V	
Continuous Drain Current (T <sub>1</sub> = 175 °C) <sup>a</sup>	T <sub>C</sub> = 25 °C		125	А	
Continuous Diain Current (1 <sub>J</sub> = 175 °C) <sup>a</sup>	T <sub>C</sub> = 100 °C	l <sub>D</sub>	110		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	400		
Single Avalanche Energy		E <sub>AS</sub>	255	mJ	
Maximum Power Dissinations	T <sub>C</sub> = 25 °C	D	150	W	
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 100 °C	- P <sub>D</sub>	75	VV	
Operating Junction and Storage Temperature Rar	nge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) <sup>d</sup>	$R_{thJA}$	45	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	1	]		

#### Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>0JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40	-	-	.,	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1	-	3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
7 0 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		$V_{DS} = 40  V,  V_{GS} = 0  V$	-	-	1	μА	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	100		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	125	-	-	Α	
Danie Course On State Beginter 2	0	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A	-	2.2	2.7		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 30 A	-	3.3	3.8	mΩ	
Forward Transconductance <sup>a</sup>	9fs	$V_{DS} = 5 \text{ V}, I_{D} = 30 \text{ A}$	-	55	-	S	
Dynamic <sup>b</sup>				<u>.                                      </u>			
Input Capacitance	C <sub>iss</sub>		-	2920	-	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	-	876	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	2	-		
Total Gate Charge <sup>c</sup>	$Q_g$		-	40.4	-		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	5.84	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	4.96	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	-	4.4	-	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	11.5	-		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 20 \text{ V}, I_D = 30 \text{ A}, R_g = 3 \Omega$	-	10	-	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	V <sub>GS</sub> = 10 V	-	40	-		
Fall Time <sup>c</sup>	t <sub>f</sub>		-	12	-		
<b>Drain-Source Body Diode Ratings and</b>	Characterist	ics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	125	Α	
Pulsed Current	I <sub>SM</sub>		-	-	400	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V	-	-	1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 30 A, di/dt = 100 A/µs	-	23	-	ns	
Reverse Recovery Charge	Q <sub>rr</sub>	$_{\text{IF}} = 30 \text{ A}, \text{ u/ut} - 100 \text{ A/} \mu\text{s}$	-	55	-	nC	

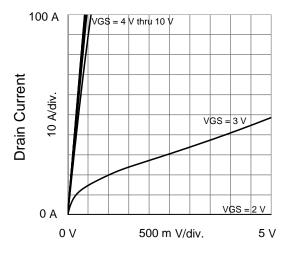
#### **Notes**

- a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

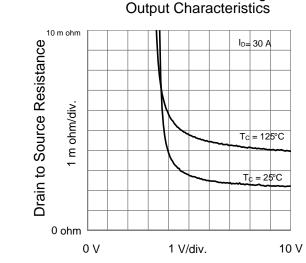
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.



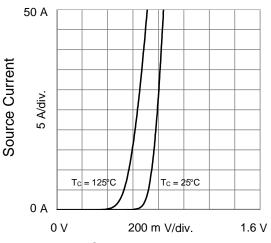
#### TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)



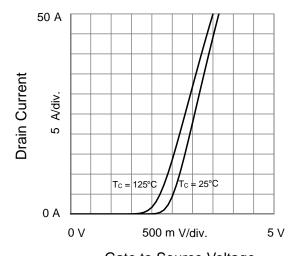
Drain to Source Voltage **Output Characteristics** 



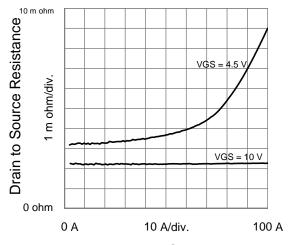
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltag



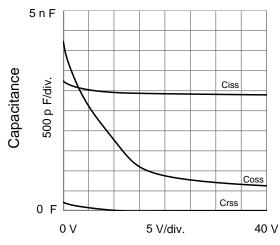
Source to Drain Voltage **Body Diode Forward Characteristics** 



Gate to Source Voltage Transfer Characteristics



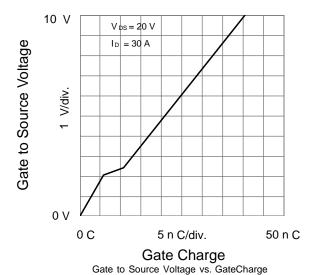
**Drain Current** 

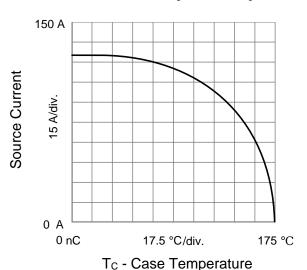


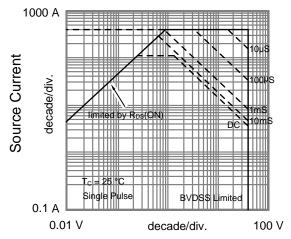
Drain to Source Voltage Capacitances



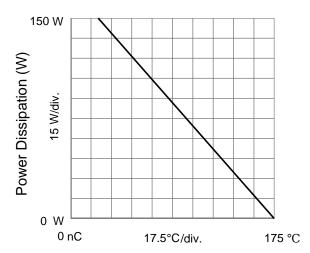
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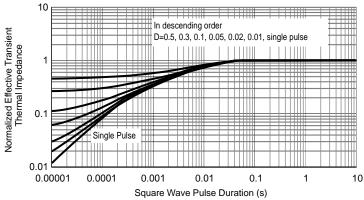




Source to Drain Voltage Safe Operating Area, Junction-to-Case



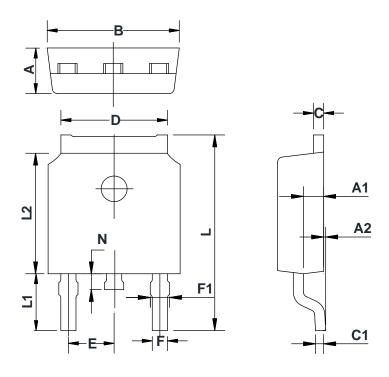
T<sub>C</sub> - Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case

Din-Tek SEMICONDUCTOR

# TO-252-2L PACKAGE OUTLINE



**COMMON DIMENSIONS** (UNITS OF MEA SURE=MILLIMETER)

O. mala al	B.4:	T	N.4	
Symbol	Min	Тур	Max	
Α	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
С	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
E	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.40	2.80	3.60	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	





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